

TRANSISTOR (NPN)

FEATURES

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary types: BCP51 ... BCP53 (PNP)

SOT-223



- 1. BASE
- 2. COLLECTOR
- 3. EMITTER

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	BCP54	BCP55	BCP56	Units
V _{CBO}	Collector-Base Voltage	45	60	100	V
V _{CEO}	Collector-Emitter Voltage	45	60	80	V
V _{EBO}	Emitter-Base Voltage	5		V	
Ic	Collector Current -Continuous	1		Α	
Pc	Collector Power Dissipation	1.5		W	
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	94		°C/W	
T _{stg}	Storage Temperature Range	-65to+150		℃	

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter		Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	BCP54			45		
	BCP55	$V_{(BR)CBO}$	I _C = 0.1mA,I _E =0	60		V
	BCP56			100		
Collector-emitter breakdown voltage BCP54				45		
	BCP55	$V_{(BR)CEO}$	I _C = 10mA,I _B =0	60		V
	BCP56			80		
Base-emitter breakdown voltage		$V_{(BR)EBO}$	I _C = 10μΑ,I _E =0	5		٧
Collector cut-off current		I _{CBO}	V _{CB} = 30 V, I _E =0		100	nA
		h _{FE(1)}	V _{CE} = 2V, I _C =5mA	25		
DC current gain		h _{FE(2)}	V _{CE} = 2V, I _C =150m A	63	250	
		h _{FE(3)}	V _{CE} = 2V, I _C =500m A	25		
Collector-emitter saturation voltage		V _{CE(sat)}	I _C =500mA,I _B =50mA		0.5	٧
Base-emitter voltage		V _{BE}	V _{CE} =2V, I _C =500m A		1	٧
Transition frequency		f _T	V _{CE} =10V,I _C =50mA,f=100MHz	100		MHz

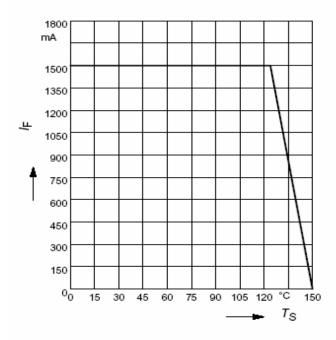
CLASSIFICATION OF h_{FE(2)}

Rank	BCP54-10, BCP55-10, BCP56-10	BCP54-16, BCP55-16, BCP56-16		
Range 63-160		100-250		



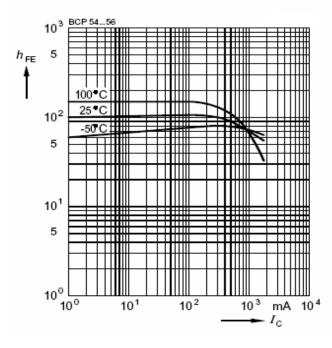
Typical Characteristics

Total power dissipation $P_{tot} = f(T_S)$



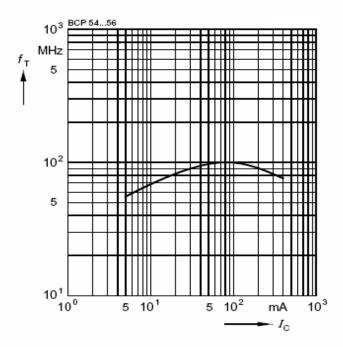
DC current gain $h_{FE} = f(I_C)$

$$V_{CE} = 2V$$



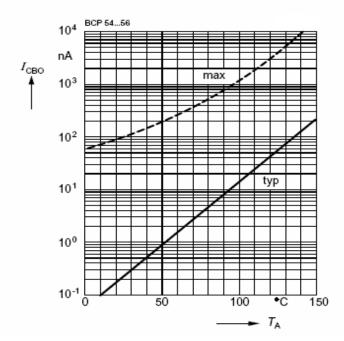
Transition frequency $f_T = f(I_C)$

$$V_{CE} = 10V$$



Collector cutoff current $I_{CBO} = f(T_A)$

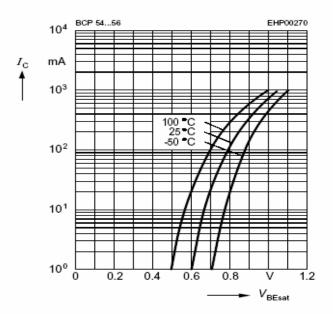
$$V_{CB} = 30V$$





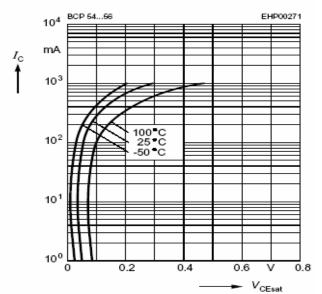
Base-emitter saturation voltage

$$I_{C} = f(V_{BEsat}), h_{FE} = 10$$



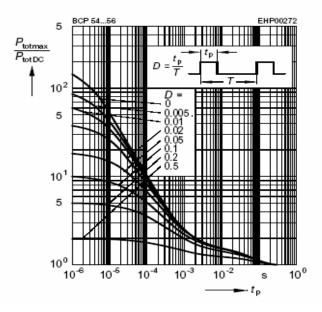
Collector-emitter saturation voltage

$$I_{\text{C}} = f(V_{\text{CEsat}}), h_{\text{FE}} = 10$$



Permissible pulse load

 $P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$



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